

In the Claims

Claims 1-52 (canceled).

53. (new) A method for providing a capacitance between a first node and a second node on a semiconductor substrate, the method comprising:

forming a plurality of layers of conductive strips on the substrate;

configuring each of the layers to have a plurality of conductive strips, with the conductive strips in each layer being alternately connected to the first and second nodes,

forming a conductive plate adjacent to the plurality of layers of conductive strips; and

coupling the conductive plate to one of the nodes.

54. (new) The method of claim 53, wherein the plurality of layers of conductive strips are aligned so that strips connected to the first node lie above strips connected to the second node.

55. (new) The method of claim 53, wherein the conductive plate is disposed beneath the lowest of the plurality of layers of conductive strips.

56. (new) The method of claim 55, the method further comprising forming a second conductive plate disposed above the highest of the plurality of layers of conductive strips.

57. (new) The method of claim 56, wherein the conductive plate is coupled to the first node and the second conductive plate is coupled to the second node.

58. (new) The method of claim 56, wherein the conductive plate is coupled to the first node and the second conductive plate is also coupled to the first node.

59. (new) The method of claim 53, wherein the conductive plate is disposed above the highest of the plurality of layers of conductive strips.
60. (new) The method of claim 53, wherein the conductive plate is disposed to the side of the plurality of layers of conductive strips.
61. (new) A method of shielding a capacitor structure formed on a semiconductor substrate, the capacitor structure providing capacitance between a first node and a second node, the method comprising:
forming one or more layers of conductive strips on the substrate;
configuring each of the layers to have a plurality of conductive strips, with each of the conductive strips in each layer being connected to one of the first or second nodes, and
forming a conductive shield adjacent to the capacitor structure for shielding the capacitor structure.
62. (new) The method of claim 61, further comprising connecting the conductive shield to the first node.
63. (new) The method of claim 61, further comprising configuring the conductive strips in each layer to be alternately connected to the first and second nodes.
64. (new) The method of claim 63, wherein the one or more of layers of conductive strips are aligned so that strips connected to the first node lie above strips connected to the second node.

65. (new) The method of claim 61, wherein the conductive shield is disposed beneath the lowest of the one or more layers of conductive strips.
66. (new) The method of claim 65, the method further comprising forming a second conductive shield disposed above the highest of the one or more layers of conductive strips.
67. (new) A method of providing a power amplifier for amplifying signals in an RF apparatus, the method comprising:
- forming a power amplifier circuit on a semiconductor substrate, the power amplifier circuit having first and second nodes;
 - forming one or more layers of conductive strips on the substrate;
 - configuring each of the layers to have a plurality of conductive strips, with each of the conductive strips in each layer being connected to one of the first or second nodes to provide a capacitance between the first and second nodes;
 - forming a conductive shield adjacent to the capacitor structure for shielding the capacitor structure; and
 - coupling the conductive shield to one of the nodes.
68. (new) The method of claim 67, further comprising connecting the conductive shield to the first node.
69. (new) The method of claim 67, further comprising configuring the conductive strips in each layer to be alternately connected to the first and second nodes.

70. (new) The method of claim 69, wherein the one or more of layers of conductive strips are aligned so that strips connected to the first node lie above strips connected to the second node.

71. (new) The method of claim 67, wherein the conductive shield is disposed beneath the lowest of the one or more layers of conductive strips.

72. (new) The method of claim 71, the method further comprising forming a second conductive shield disposed above the highest of the one or more layers of conductive strips.